



**UNIVERSITI PUTRA MALAYSIA**

**POTENTIOSTATIC, CYCLIC VOLTAMMETRIC AND PULSED  
ELECTRODEPOSITION OF CADMIUM SELENIDE THIN FILMS**

**NORHIDAYAH AHMAD WAZIR**

**FS 2010 54**

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By

**NORHIDAYAH AHMAD WAZIR**

Thesis Submitted in Fulfillment of the Requirement for the  
Degree of Master of Science in the  
Faculty of Science Universiti Putra Malaysia

**March 2010**

Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfillment of the requirement for the degree of Master of Science

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**Chairman : Profesor Zulkarnain bin Zainal,  
Faculty : Science**

Cadmium selenide thin films were electrodeposited on the indium tin oxide (ITO) conducting glass substrate from an electrolyte containing of  $\text{CdSO}_4$  and  $\text{SeO}_2$  by potentiostatic (PSD), cyclic voltammetric (CVD) and pulsed electrodeposition (PED) technique. The cyclic voltammetry experiments were also carried out to determine the range of potential for deposition of CdSe through potentiostatic and pulse techniques. Potentiostatic electrodeposition experiments have been carried out at varying deposition potential, deposition time and bath temperature. For CVD the effect of varying the number of cycle, scan rate, and deposition at different bath temperature were studied. While the effect of different pulse potential and duty cycles were investigated for PED.

X-ray diffraction confirmed that polycrystalline CdSe of hexagonal structure was formed on the ITO substrate for PSD technique, while for CVD and PED technique, mixture of hexagonal and cubic CdSe phase were observed. The films exhibited n-type

semiconducting behavior for PSD but p-type for CVD. Heating the sample prepared by CVD at 550°C, removes unwanted selenium element, enhanced the morphology of the film and changed the semiconducting behavior from p-type to n-type. More interesting, as deposited PED films showed both n-type and p-type behavior based on their response to the light illumination. SEM micrograph confirmed the polycrystalline nature of all deposits. In these three techniques, the photoactivity, composition, grain size and shape of the film were found to be dependent on the electrodeposition condition.

CdSe thin film was successfully obtained from the mixture of 0.06 M CdSO<sub>4</sub> and 0.005 M of SeO<sub>2</sub> solution at potential -0.68V vs Ag/AgCl for preparation through PSD. Thicker films were formed at prolong deposition time. The PSD of CdSe was most suitable to be carried out at room temperature. Lower number of cycle and scan rate are preferable for CVD, with potential range between -1.0V to 1.0V. Smooth and well adherent samples were obtained. CVD technique produces selenium rich sample. But the excess of selenium could be eliminated by calcination at 550°C. PED produces smooth and compact films at -0.8V with 50% duty cycles. Among these three techniques, potentiostatic was found to be able to produce nearly stoichiometric of CdSe thin films. The optical absorption studies revealed that all films have direct optical band gap energy values, E<sub>g</sub>, in the range of 1.7 to 2.0 eV.

Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Master Sains.

**ELEKTROENAPAN POTENSIOSTATIK FILM NIPIS CADMIUM SELENIDE  
MELALUI TEKNIK VOLTAMMETRI KITARAN DAN DENYUTAN**

Oleh

**NORHIDAYAH AHMAD WAZIR**

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**Pengerusi : Profesor Zulkarnain bin Zainal, PhD**

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Kadmium selenida telah dielektroenapkan di atas kepingan indium tin oxide (ITO) daripada larutan elektrolit yang mengandungi  $\text{CdSO}_4$  and  $\text{SeO}_2$  melalui teknik enapan potensiostatik (PSD), enapan voltammetrik kitaran (CVD) dan enapan denyutan (PED).

Eksperimen siklik voltammetri dibuat untuk menentukan julat keupayaan untuk pengelektroenapan CdSe melalui kaedah potensiostatik (PSD) dan enapan denyutan (PED). Kesan perubahan beberapa parameter telah dikaji semasa eksperimen (PSD) iaitu keupayaan penganapan, jangka masa penganapan, dan suhu elektrolit. Bagi elektroenapan CVD, kesan mengubah bilangan kitaran, kadar imbasan dan suhu elektrolit yang berbeza dikaji. Sementara itu, kesan magnitud keupayaan denyutan, kitaran kerja tempoh denyutan dan kesan suhu elektrolit yang berbeza juga dikaji.

Analisis XRD mengesahkan, polihablur heksagonal CdSe terhasil di atas kepingan ITO bagi elektroenapan PSD. Manakala bagi teknik enapan CVD dan PED, campuran struktur heksagonal dan kubik terbentuk. Filem-filem yang diperoleh dari teknik potensiostatik didapati mempamerkan sifat semikonduktor jenis - n. Bagi teknik CVD, ia mempamerkan jenis p dan berubah kepada n setelah dipanaskan pada suhu di sekitar 550°C. Filem yang diperoleh melalui PED memiliki kedua-dua jenis n dan p berdasarkan respon kepada cahaya. Dalam ketiga-tiga teknik ini, fotoaktiviti, komposisi, saiz dan bentuk hablur didapati bergantung kepada keadaan elektroenapan.

CdSe telah dienapkan daripada larutan 0.06M CdSO<sub>4</sub> an 5mM of SeO<sub>2</sub> pada keupayaan -0.68V terhadap Ag/AgCl bagi penyediaan melalui kaedah PSD. Filem yang lebih tebal diperoleh apabila masa elektroenapan dipanjangkan. Bagaimanapun, bagi teknik ini, penyediaan filem lebih sesuai dijalankan pada suhu bilik. Bilangan kitaran dan kadar imbasan yang rendah lebih sesuai untuk mengenakan CdSe melalui CVD. Teknik ini menghasilkan sampel yang kaya selenium. Walaubagaimanapun, selenium boleh disingkirkan melalui pemanasan filem nipis pada suhu 550°C. Teknik PED menghasilkan filem yang rata dan padat pada keupayaan -0.80 V dengan 50% kitar kerja. Elektroenapan CdSe dengan kaedah ini juga lebih sesuai dilakukan pada suhu bilik.

Diantara ketiga-tiga teknik ini, PSD didapati boleh menghasilkan filem yang hampir stoikiometri. Serapan optikal menunjukkan semua filem yang diperolehi memiliki ruang tenaga bagi peralihan terus dalam lingkungan 1.70 to 2.10 eV.



## ACKNOWLEDGEMENTS

Allhamdulillah, Praise be to Allah.

First of all, I would like to express my sincere appreciation and utmost gratitude to the chairman of the M. Sc. Project, Professor Dr. Zulkarnain Zainal for his continuous assistance, guidance and motivation. Without which this project might not have come to completion. I like to also acknowledge the help and guidance of my co-supervisors, Associate professor Dr. Tan Wee Tee.

Also worthy of acknowledgement, are the staff of department of chemistry (UPM) and Bioscience, En Raffi and Pn Ida for their kind cooperation. Many thanks also go to my laboratory mate who helped me a lot and being nice to me especially Teo Seok Liang, Koo Chee Siong, Chang Sook Keng, Alvin Chong Jin Kai and Mohd Fairul Sharin.

Among others who deserve of this acknowledgement are my respected and beloved parents En Ahmad Wazir and Pn Zuyah, my siblings and to the special person, Mohd Misrul who had been worried and gave a constant push when I had oftentimes giving up, I also wish to thank to my superiors in Petronas Research Sdn Bhd (PRSB), En Makhzan Selamat , En Ismail Yusoff , En Mustaffa Abdullah, and not to forget, Puan Noor Azlenawati who had given me chance to write up this thesis in office, during working hours for one month. They really deserved this high appreciation.



Finally, it is a must for me to express thanks to financial support of this research and PASCA scholarship. I also must thank all the kind help of the staff at School of Graduate Studies (SGS) Universiti Putra Malaysia, It is the help of you people that makes graduating possible.



I certify that a Thesis Examination Committee has met on \_\_\_\_\_ to conduct the final examination of Norhidayah Ahmad Wazir on her Master of Science thesis entitle “Potentiostatic, Cyclic Voltammetric and Pulsed Electrodeposition of Cdse Thin Films” in accordance with Universities and University Colleges Act 1971 and the Constitution of the Universiti Putra Malaysia [P.U.(A) 106] 15 March 1998. The Committee recommends that the student be awarded the Master degree.

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Date: 15 July 2010

## DECLARATION

I hereby declare that the thesis is based on my original work except for quotations and citations which have been duly acknowledged. I also declare that it has not been previously or concurrently submitted for any other degree at Universiti Putra Malaysia or other institutions



**NORHIDAYAH AHMAD WAZIR**

**Date :**

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